## Z Q Zheng

## List of Publications by Citations

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#	Paper	IF	Citations
76	Stable, highly-responsive and broadband photodetection based on large-area multilayered WS2 films grown by pulsed-laser deposition. <i>Nanoscale</i> , <b>2015</b> , 7, 14974-81	7.7	217
75	Flexible, transparent and ultra-broadband photodetector based on large-area WSe2 film for wearable devices. <i>Nanotechnology</i> , <b>2016</b> , 27, 225501	3.4	187
74	All-Layered 2D Optoelectronics: A High-Performance UVIIIs BIR Broadband SnSe Photodetector with Bi2Te3 Topological Insulator Electrodes. <i>Advanced Functional Materials</i> , <b>2017</b> , 27, 1701823	15.6	180
73	Light-controlling, flexible and transparent ethanol gas sensor based on ZnO nanoparticles for wearable devices. <i>Scientific Reports</i> , <b>2015</b> , 5, 11070	4.9	142
72	Electronic Reconstruction of Ag2WO4 Nanorods for Visible-Light Photocatalysis. <i>ACS Nano</i> , <b>2015</b> , 9, 7256-65	16.7	120
71	Layered-material WS2/topological insulator Bi2Te3 heterostructure photodetector with ultrahigh responsivity in the range from 370 to 1550 nm. <i>Journal of Materials Chemistry C</i> , <b>2016</b> , 4, 7831-7840	7.1	107
70	Promoting the Performance of Layered-Material Photodetectors by Alloy Engineering. <i>ACS Applied Materials &amp; Amp; Interfaces</i> , <b>2016</b> , 8, 12915-24	9.5	103
69	Production of large-area 2D materials for high-performance photodetectors by pulsed-laser deposition. <i>Progress in Materials Science</i> , <b>2019</b> , 106, 100573	42.2	94
68	Promoting Photosensitivity and Detectivity of the Bi/Si Heterojunction Photodetector by Inserting a WS2 Layer. <i>ACS Applied Materials &amp; Description</i> (1997) 11-12. ACS Applied Materials & Description (1997) 12-12. ACS Applied Materials & Description (1997) 13-12. ACS Applied Materials & Descripti	9.5	78
67	Growth of centimeter-scale high-quality In2Se3 films for transparent, flexible and high performance photodetectors. <i>Journal of Materials Chemistry C</i> , <b>2016</b> , 4, 8094-8103	7.1	72
66	Self-Assembly High-Performance UV-vis-NIR Broadband 🛭 nSe/Si Photodetector Array for Weak Signal Detection. <i>ACS Applied Materials &amp; amp; Interfaces</i> , <b>2017</b> , 9, 43830-43837	9.5	71
65	Layered tin monoselenide as advanced photothermal conversion materials for efficient solar energy-driven water evaporation. <i>Nanoscale</i> , <b>2018</b> , 10, 2876-2886	7.7	70
64	Self-assembled and Pd decorated Zn2SnO4/ZnO wire-sheet shape nano-heterostructures networks hydrogen gas sensors. <i>Sensors and Actuators B: Chemical</i> , <b>2014</b> , 195, 549-561	8.5	62
63	Stable, Fast UV-Vis-NIR Photodetector with Excellent Responsivity, Detectivity, and Sensitivity Based on <code>Bn2Te3</code> Films with a Direct Bandgap. <i>ACS Applied Materials &amp; Direct Bandgap. Interfaces</i> , <b>2016</b> , 8, 20872-9	9.5	58
62	Centimeter-Scale Deposition of MoWSe Alloy Film for High-Performance Photodetectors on Versatile Substrates. <i>ACS Applied Materials &amp; Description</i> (2017), 14920-14928	9.5	57
61	A Floating Sheet for Efficient Photocatalytic Water Splitting. Advanced Energy Materials, 2016, 6, 16005	<b>1.0</b> r.8	54
60	Broadband photodetectors based on 2D group IVA metal chalcogenides semiconductors. <i>Applied Materials Today</i> , <b>2019</b> , 15, 115-138	6.6	50

## (2018-2017)

59	Alloying-assisted phonon engineering of layered BiInSe@nickel foam for efficient solar-enabled water evaporation. <i>Nanoscale</i> , <b>2017</b> , 9, 16396-16403	7.7	49	
58	Tin dioxide quantum dots coupled with graphene for high-performance bulk-silicon Schottky photodetector. <i>Materials Horizons</i> , <b>2018</b> , 5, 727-737	14.4	46	
57	Low-temperature and highly sensitive C2H2 sensor based on Au decorated ZnO/ln2O3 belt-tooth shape nano-heterostructures. <i>Sensors and Actuators B: Chemical</i> , <b>2017</b> , 244, 344-356	8.5	44	
56	2D In S Nanoflake Coupled with Graphene toward High-Sensitivity and Fast-Response Bulk-Silicon Schottky Photodetector. <i>Small</i> , <b>2019</b> , 15, e1904912	11	44	
55	A red phosphor Mg3Y2Ge3O12: Bi3+, Eu3+ with high brightness and excellent thermal stability of luminescence for white light-emitting diodes. <i>Journal of Luminescence</i> , <b>2019</b> , 210, 202-209	3.8	44	
54	Synergistic Effect of Hybrid Multilayer In2Se3 and Nanodiamonds for Highly Sensitive Photodetectors. <i>ACS Applied Materials &amp; </i>	9.5	41	
53	Self-Assembly of the Lateral InSe/CuInSe Heterojunction for Enhanced Photodetection. <i>ACS Applied Materials &amp; District Action Self-Assembly of the Lateral InSe/CuInSe Heterojunction for Enhanced Photodetection. ACS Applied Materials &amp; District Action Self-Assembly of the Lateral InSe/CuInSe Heterojunction for Enhanced Photodetection. <i>ACS Applied Materials &amp; District Action Self-Assembly of the Lateral InSe/CuInSe Heterojunction for Enhanced Photodetection. ACS Applied Materials &amp; District Action Self-Assembly of the Lateral InSe/CuInSe Heterojunction for Enhanced Photodetection. <i>ACS Applied Materials &amp; District Action Self-Assembly Self</i></i></i>	9.5	39	
52	Light-controlled C2H2 gas sensing based on AuInO nanowires with plasmon-enhanced sensitivity at room temperature. <i>Journal of Materials Chemistry C</i> , <b>2015</b> , 3, 7067-7074	7.1	38	
51	Self-Powered SnSSe Alloy/Silicon Heterojunction Photodetectors with High Sensitivity in a Wide Spectral Range. <i>ACS Applied Materials &amp; amp; Interfaces</i> , <b>2019</b> , 11, 40222-40231	9.5	37	
50	Strain engineering coupled with optical regulation towards a high-sensitivity In2S3 photodetector. <i>Materials Horizons</i> , <b>2020</b> , 7, 1427-1435	14.4	32	
49	In2O 3 Nanotower Hydrogen Gas Sensors Based on Both Schottky Junction and Thermoelectronic Emission. <i>Nanoscale Research Letters</i> , <b>2015</b> , 10, 1002	5	31	
48	Non-layered 2D materials toward advanced photoelectric devices: progress and prospects. <i>Materials Horizons</i> , <b>2020</b> , 7, 2185-2207	14.4	30	
47	UVII is-NIR photodetector based on monolayer MoS2. <i>Materials Letters</i> , <b>2019</b> , 237, 298-302	3.3	28	
46	Graphene/In2S3 van der Waals Heterostructure for Ultrasensitive Photodetection. <i>ACS Photonics</i> , <b>2018</b> , 5, 4912-4919	6.3	28	
45	Ultrasensitive 2D/3D Heterojunction Multicolor Photodetectors: A Synergy of Laterally and Vertically Aligned 2D Layered Materials. <i>ACS Applied Materials &amp; Description</i> (2018), 10, 38166-38172	9.5	26	
44	Thickness-Dependent Optical Properties and In-Plane Anisotropic Raman Response of the 2D En2S3. <i>Advanced Optical Materials</i> , <b>2019</b> , 7, 1901085	8.1	25	
43	2D WS2 Based Asymmetric Schottky Photodetector with High Performance. <i>Advanced Electronic Materials</i> , <b>2021</b> , 7, 2000964	6.4	24	
42	Out of plane stacking of InSe-based heterostructures towards high performance electronic and optoelectronic devices using a graphene electrode. <i>Journal of Materials Chemistry C</i> , <b>2018</b> , 6, 12509-125	577 <sup>-</sup>	24	

41	Unique and Tunable Photodetecting Performance for Two-Dimensional Layered MoSe/WSe p-n Junction on the 4H-SiC Substrate. <i>ACS Applied Materials &amp; Amp; Interfaces</i> , <b>2019</b> , 11, 19277-19285	9.5	23
40	An asymmetric contact-induced self-powered 2D InS photodetector towards high-sensitivity and fast-response. <i>Nanoscale</i> , <b>2020</b> , 12, 7196-7205	7.7	23
39	Fabrication of a high performance ZnIn2S4/Si heterostructure photodetector array for weak signal detection. <i>Journal of Materials Chemistry C</i> , <b>2018</b> , 6, 12928-12939	7.1	20
38	Epitaxial growth of large-scale In2S3 nanoflakes and the construction of a high performance In2S3/Si photodetector. <i>Journal of Materials Chemistry C</i> , <b>2019</b> , 7, 12104-12113	7.1	19
37	An Innovative Postdeposition Annealing Approach Producing Centimeter-Scale In2O3/In2(TeO3)3 Bulk Heterojunction Thin Film for Room-Temperature Persistent Photoconductivity. <i>Advanced Optical Materials</i> , <b>2017</b> , 5, 1600908	8.1	17
36	Novel two-dimensional monoelemental and ternary materials: growth, physics and application. <i>Nanophotonics</i> , <b>2020</b> , 9, 2147-2168	6.3	17
35	A flexible, transparent and high-performance gas sensor based on layer-materials for wearable technology. <i>Nanotechnology</i> , <b>2017</b> , 28, 415501	3.4	17
34	All-Dielectric Nanostructure Fabry <b>P</b> fot-Enhanced Mie Resonances Coupled with Photogain Modulation toward Ultrasensitive In2S3 Photodetector. <i>Advanced Functional Materials</i> , <b>2021</b> , 31, 20079	98 <sup>75.6</sup>	17
33	High performance tin diselenide photodetectors dependent on thickness: a vertical graphene sandwiched device and interfacial mechanism. <i>Nanoscale</i> , <b>2019</b> , 11, 13309-13317	7.7	15
32	Plasmon resonances in semiconductor materials for detecting photocatalysis at the single-particle level. <i>Nanoscale</i> , <b>2016</b> , 8, 15001-7	7.7	15
31	Controllable growth of large-area atomically thin ReS2 films and their thickness-dependent optoelectronic properties. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 153102	3.4	14
30	Tunable Polarity Behavior and High-Performance Photosensitive Characteristics in Schottky-Barrier Field-Effect Transistors Based on Multilayer WS. <i>ACS Applied Materials &amp; Discourse (Material &amp; Discours)</i> , 10, 2745	- <del>2</del> 751	13
29	Field emission properties and growth mechanism of In2O3 nanostructures. <i>Nanoscale Research Letters</i> , <b>2014</b> , 9, 111	5	12
28	Recent progress in high-performance photo-detectors enabled by the pulsed laser deposition technology. <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 4988-5014	7.1	11
27	Self-assembly In2Se3/SnSe2 heterostructure array with suppressed dark current and enhanced photosensitivity for weak signal. <i>Science China Materials</i> , <b>2020</b> , 63, 1560-1569	7.1	11
26	Field emission and growth mechanism of ZnO microrods array with nanospikes fabricated by thermal evaporation. <i>Materials Letters</i> , <b>2016</b> , 170, 210-212	3.3	9
25	3D resonator based on luminescence enhanced by both polarized, size-dependent whispering gallery modes and Fabry-Pflot waveguide modes in individual ZnO micro- and nanonails. <i>Nanoscale</i> , <b>2014</b> , 6, 5338-42	7.7	9
24	Vertically stacked BiSe/MoTe heterostructure with large band offsets for nanoelectronics.  Nanoscale, 2021, 13, 15403-15414	7.7	9

23	Universal Strategy Integrating Strain and Interface Engineering to Drive High-Performance 2D Material Photodetectors. <i>Advanced Optical Materials</i> , <b>2021</b> , 9, 2100450	8.1	8
22	Field emission and photoluminescence of ZnO nanocombs. <i>Applied Physics A: Materials Science and Processing</i> , <b>2013</b> , 113, 549-556	2.6	7
21	Whispering gallery and Fabry <b>P</b> flot modes enhanced luminescence from individual ZnO micro mushroom. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 034313	2.5	6
20	A reasonably designed 2D WS and CdS microwire heterojunction for high performance photoresponse. <i>Nanoscale</i> , <b>2021</b> , 13, 5660-5669	7.7	6
19	Promoting the Performance of 2D Material Photodetectors by Dielectric Engineering <i>Small Methods</i> , <b>2021</b> , e2101046	12.8	6
18	Polarity-Switchable and Self-Driven Photo-Response Based on Vertically Stacked Type-III GeSe/SnS 2 Heterojunction. <i>Advanced Materials Interfaces</i> ,2102099	4.6	5
17	Enhancement of exciton emission in WS based on the Kerker effect from the mode engineering of individual Si nanostripes. <i>Nanoscale Horizons</i> , <b>2020</b> , 5, 1368-1377	10.8	4
16	Pulsed-Laser-Deposition Fabricated ZnIn 2 S 4 Photodetectors with Excellent ON/OFF Switching Characteristics toward High-Temperature-Resistant Photodetection Applications. <i>Advanced Optical Materials</i> ,2102335	8.1	4
15	Hybrid 1D/2D heterostructure with electronic structure engineering toward high-sensitivity and polarization-dependent photodetector. <i>Science China Materials</i> , <b>2022</b> , 65, 732-740	7.1	4
14	Deep insights into interface engineering by buffer layer for efficient perovskite solar cells: a first-principles study. <i>Science China Materials</i> , <b>2020</b> , 63, 1588-1596	7.1	3
13	Circular SnS0.5Se0.5 Nanosheets with Highly Anisotropic Performance for Nanoelectronics. <i>ACS Applied Nano Materials</i> , <b>2020</b> , 3, 10270-10283	5.6	3
12	Large-area ReS2 monolayer films on flexible substrate for SERS based molecular sensing with strong fluorescence quenching. <i>Applied Surface Science</i> , <b>2021</b> , 542, 148757	6.7	3
11	Non-Layered Te/In S Tunneling Heterojunctions with Ultrahigh Photoresponsivity and Fast Photoresponse <i>Small</i> , <b>2022</b> , e2200445	11	3
10	Nonlayered In2S3/Al2O3/CsPbBr3 Quantum Dot Heterojunctions for Sensitive and Stable Photodetectors. <i>ACS Applied Nano Materials</i> , <b>2021</b> , 4, 5106-5114	5.6	2
9	High-quality two-dimensional tellurium flakes grown by high-temperature vapor deposition. Journal of Materials Chemistry C,	7.1	2
8	Self-driven SnSSe alloy/GaAs heterostructure based unique polarization sensitive photodetectors. <i>Nanoscale</i> , <b>2021</b> , 13, 15193-15204	7.7	2
7	Optical Resonance Coupled with Electronic Structure Engineering toward High-Sensitivity Photodetectors. <i>Advanced Optical Materials</i> , <b>2021</b> , 9, 2101374	8.1	2
6	An artificial optoelectronic nociceptor based on In2S3 memristor. <i>Journal Physics D: Applied Physics</i> , <b>2022</b> , 55, 125401	3	2

5	Fabrication and Hydrogen Sensing Property of In2O3 Nanotowers. <i>Advanced Materials Research</i> , <b>2013</b> , 834-836, 913-916	0.5	1
4	High performance DUV-visible 4H-SiC-based multilayered SnS2 dual-mode photodetectors. <i>Journal of Materials Chemistry C</i> ,	7.1	1
3	A New Wide Bandgap Semiconductor: Carbyne Nanocrystals. <i>Advanced Functional Materials</i> , <b>2021</b> , 31, 2104254	15.6	1
2	Etching-free high-throughput intersectional nanofabrication of diverse optical nanoantennas for nanoscale light manipulation <i>Journal of Colloid and Interface Science</i> , <b>2022</b> , 622, 950-959	9.3	1

Self-Assembled Alcohol Sensor of In2O3 Nanorods. *Advanced Materials Research*, **2013**, 834-836, 46-49 0.5